



# BT139/BTA16/BTB16 Series

## 16A Triacs

三象限

3quadrants

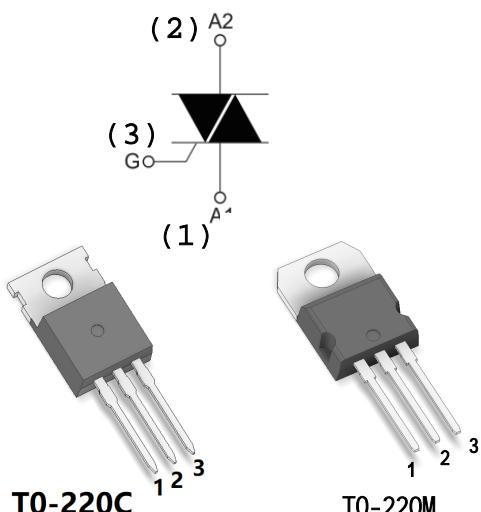
### 主要描述 GENERAL DESCRIPTION

BT139/BTA16/BTB16 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于调温调速调光，电机控制，变频电路等其它开关控制电路。

BT139/BTA16/BTB16 Triacs is fabricated using separation diffusion processes , the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability, the Triacs series is suitable for domestic lighting , heating , motor speed controllers, frequency conversion and other switch controllers.

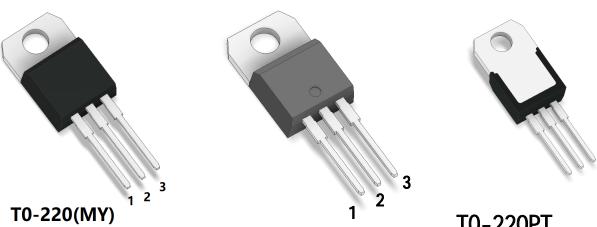
### 主要特性 MAIN FEATURES

参数 Parameter	数值 Value	单位 Unit
$V_{DRM}/V_{RRM}$	600/800	V
$I_{T(RMS)}$	16	A
$I_{GT(HI)}$	2-50	mA



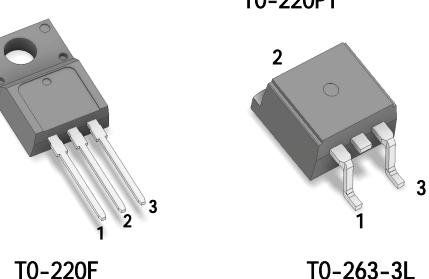
### 应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。  
domestic lighting ,heating and motor speed controllers.



### 封装形式 PACKAGE

TO-220C, TO-220M, TO-220MY, TO-220PT, TO-263-3L





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## 16A Triacs

### 极限参数(除非另有规定, Tj=25°C) ABSOLUTE RATINGS

(Tj=25°C, unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit		
I <sub>T(RMS)</sub>	RMS 通态电流 RMS on-state current(full sine wave)	Tc<=102°C	16	A	
I <sub>TSM</sub>	通态峰值浪涌电流 Non repetitive peak on-state current(full cycle)	f=50HZ	t=20ms	160	A
I <sub>2t</sub>	I <sub>2t</sub> 耗散值 I <sub>2t</sub> value for fusing		t=10ms	128	A <sub>2</sub> s
di/dt	通态电流上升率 Critical rate of rise of on-state current(I <sub>G</sub> =2×I <sub>GT</sub> , tr<=100ns)	f=120HZ	Tj=125°C	50	A/us
I <sub>GM</sub>	门极峰值电流 Peak gate current	t <sub>p</sub> =20us	Tj=125°C	4	A
P <sub>G(AV)</sub>	平均门极耗散功率 Average gate power dissipation		Tj=125°C	1	w
T <sub>STG</sub>	贮存结温范围 Storage junction temperature range		-40- +150		°C
T <sub>j</sub>	工作结温范围 Operating junction temperature range		-40- +150		°C

### 电参数(除非另有规定, Tj=25°C) ELECTRICAL CHARACTERISTICS

(Tj=25°C, unless otherwise specified)

参数 Parameter	符号 Symbol	象限 Quadrant	规范值 Value				单位 Unit	测试条件 Test Conditions
			TW	SW	CW	BW		
触发电流 Gate trigger current	I <sub>GT</sub>	I ~ III	≤5	≤10	≤35	≤50	mA	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
		IV	.....	.....	.....	.....		
触发电压 Gate trigger voltage	V <sub>GT</sub>	I ~ III	≤1.4				V	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
维持电流 Holding current	I <sub>H</sub>	I ~ III	≤15	≤25	≤40	≤60	mA	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
擎住电流 Latching current	I <sub>L</sub>		≤20	≤40	≤60	≤80	mA	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
电压上升率 Rise of off-state voltage	dv/dt		≥100	≥200	≥500	≥1000	V/ μ S	V <sub>D</sub> =2/3V <sub>DRM</sub>
通态压降 Peak on-state voltage	V <sub>TM</sub>		≤1.50				V	I <sub>T</sub> =23A
断态漏电流 Peak repetitive forward blocking current	I <sub>DRM</sub> IR <sub>RM</sub>		≤5			μ A	V <sub>RRM</sub> =V <sub>DRM</sub> , Tj = 25 ° C	V <sub>RRM</sub> =V <sub>DRM</sub> , Tj = 125 ° C
			≤0.5			mA		



热阻特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
R <sub>th(j-c)</sub>	Junction to case(AC) 芯片对管壳热阻	T0-220C/MY/M/T0-263	1.3
		T0-220PT	2.1
		T0-22F	2.2

图1 最大耗散功率与RMS通态电流关系  
Fig.1 Maximum Power Dissipation Versus

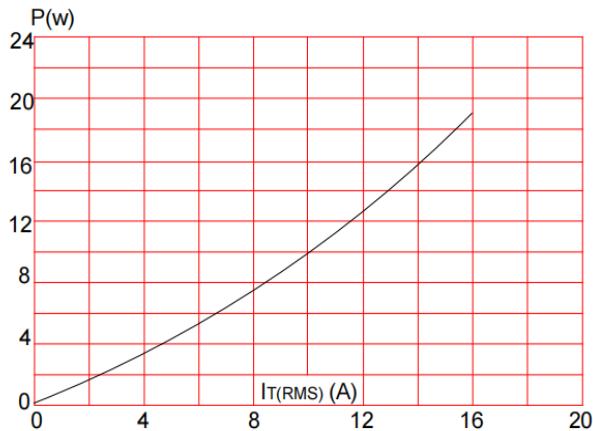


图3 通态特性  
Fig.3. On-State Characteristics

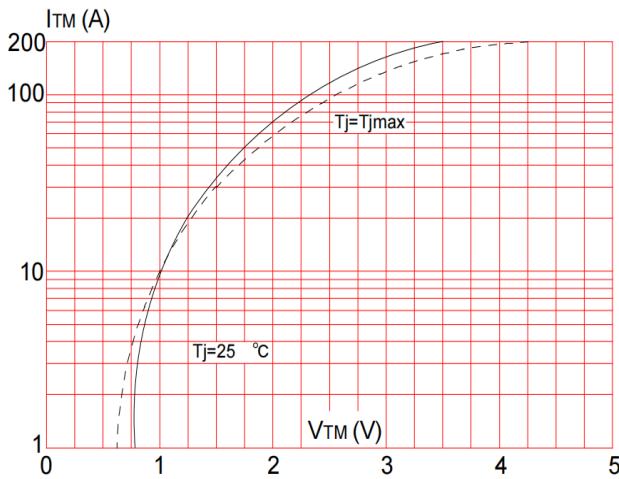


图2 IGT、IH、IL相对值 (相对于25 ) 与结温关系  
Fig.2. Relative Variation Of Gate Trigger Current  
Holding Current And Latching Current Versus Junction Temperature(Typical Value)

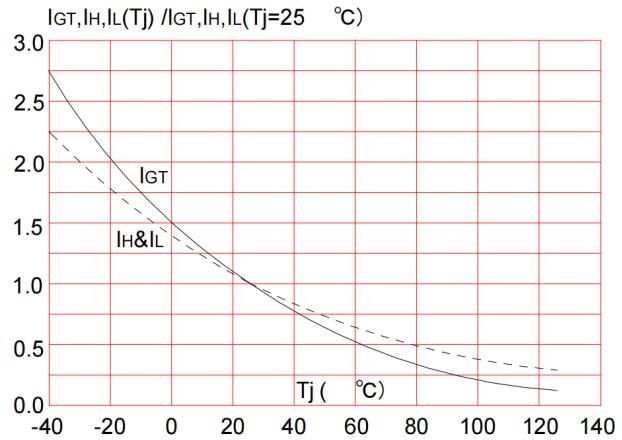
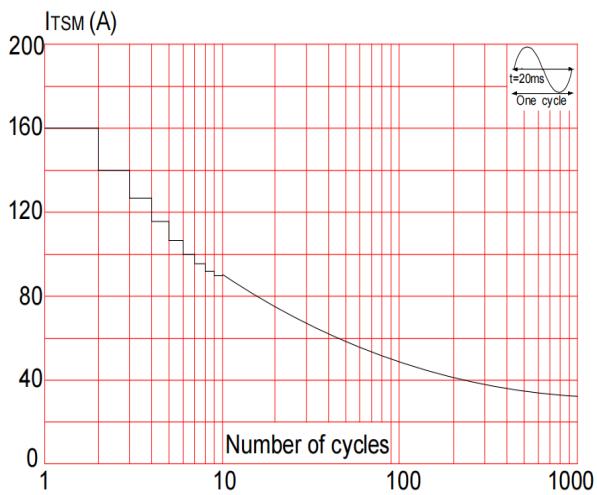


图4 通态浪涌峰值电流与周期数关系  
Fig.4. Surge Peak On-state Current Versus Number of cycle at 50Hz





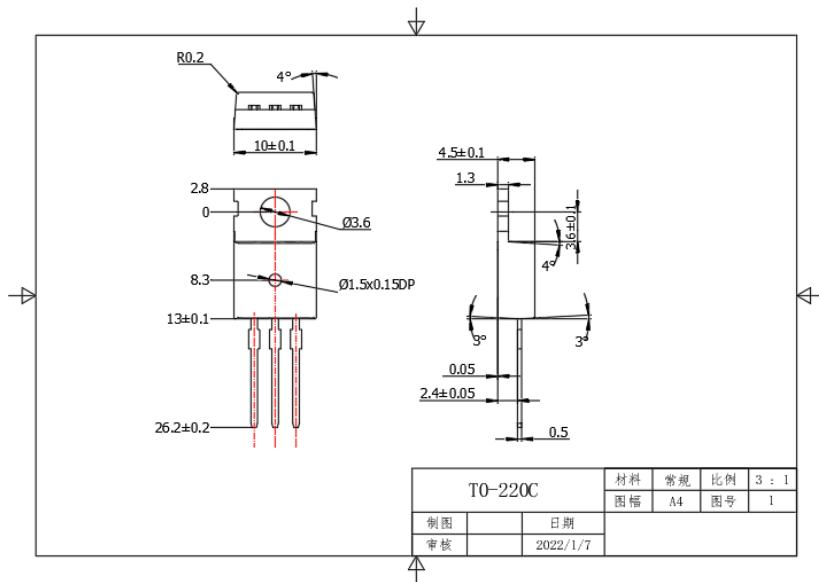
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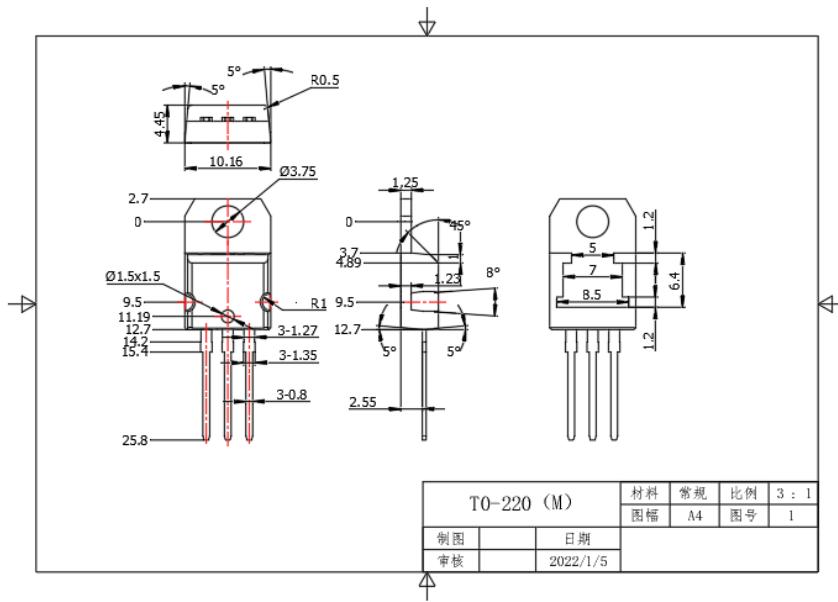
封装尺寸

PACKAGE MECHANICAL DATA

TO-220C



TO-220M



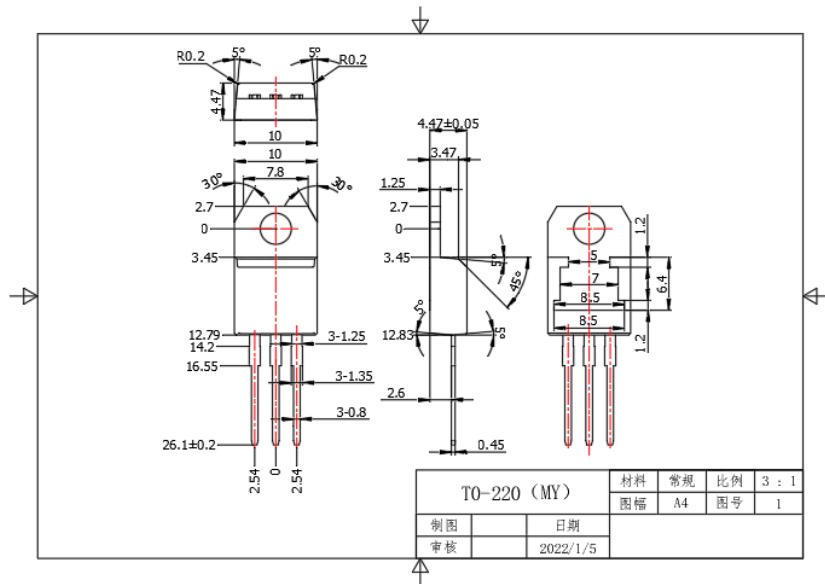


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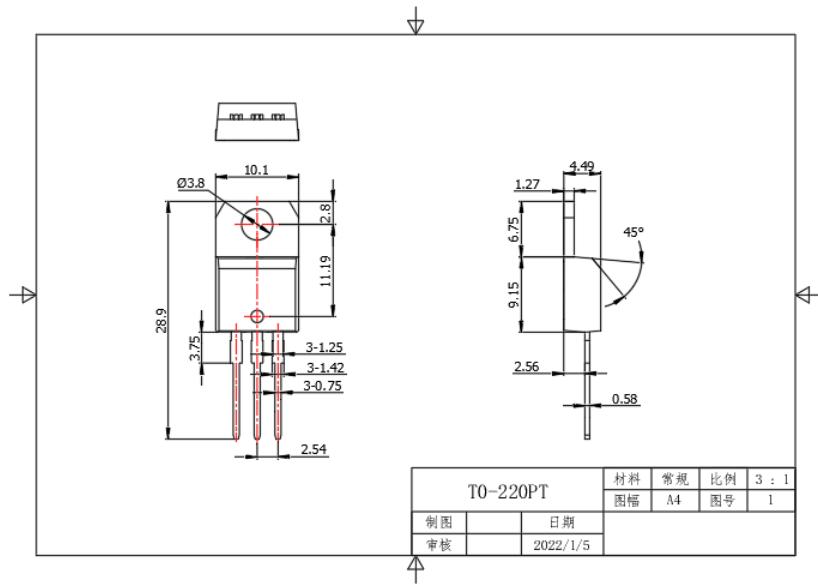
## 16A Triacs

### 封装尺寸 PACKAGE MECHANICAL DATA

TO-220MY



TO-220PT





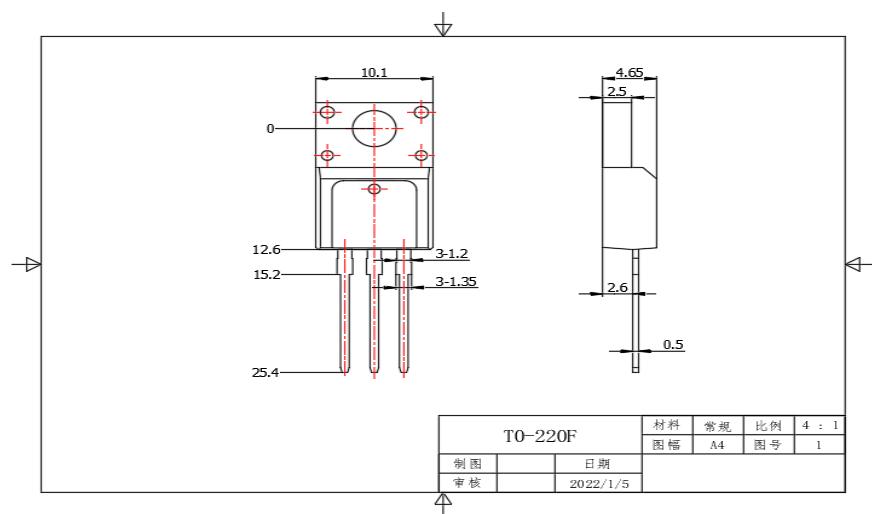
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## 16A Triacs

### 封装尺寸

### PACKAGE MECHANICAL DATA

TO-220F



TO-263-3L

